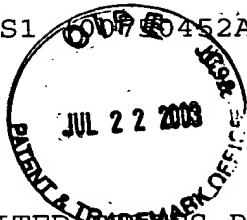


FIS920000404US1 (009 0452AA)

PATENT APPLICATION



#5  
JA  
8/1/03  
RECEIVED  
JUL 23 2003  
GROUP 1700

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Heemyong Park et al.

Serial No.: 09/924,318

Group Art Unit: 1765

Filed: August 8, 2001

Examiner: B. Tran

For: METHOD OF BUILDING A CMOS STRUCTURE ON THIN SOI  
WITH SOURCE/DRAIN ELECTRODES FORMED BY IN SITU  
DOPED SELECTIVE AMORPHOUS SILICON

Commissioner for Patents  
United States Patent and Trademark Office  
P. O. Box 1450  
Alexandria, Virginia 22313-1450

#### RESPONSE TO REQUIREMENT FOR RESTRICTION

Sir:

In response to the Office Action mailed June 23, 2003, Applicants hereby provisionally elect the invention, as identified by the Examiner of Group I, claims 1 - 4, without traverse, for further action on the merits.

#### REMARKS

Claims 1 - 7 remain active in this application. No new matter has been introduced into the application.

Restriction has been required between the inventions, as identified by the Examiner of Group I, claims 1 - 4 drawn to a manufacturing method, and Group II, claims 5 - 7, drawn to a semiconductor device. A provisional election of the invention of Group I has been provisionally made, without traverse, above. Claims 5 - 7 have not been canceled pending the filing of a divisional application.

Since the above election constitutes a complete response to the requirement for restriction and no